L Number	Hits	Search Text	DB	Time stamp
1	73	"6140226"	USPAT;	2004/06/16 17:58
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
2	0	"6140226" and "Sioc-h"	USPAT;	2004/06/16 17:58
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	0	257/758 and "SiOC-H"	USPAT;	2004/06/16 18:01
1			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
4	2	257/\$.ccls. and "SiOC-H"	USPAT;	2004/06/16 18:01
3		25774.ccis. and 510c-n	US-PGPUB;	2004/00/10 18:01
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
5	3	438/\$.ccls. and "SiOC-H"	USPAT;	2004/06/16 17:59
	_		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	0	361/\$.ccls. and "SiOC-H"	USPAT;	2004/06/16 17:59
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	0	20/63	IBM_TDB USPAT;	2004/06/16 17:59
7	"	29/\$.ccls. and "SiOC-H"	US-PGPUB;	2004/06/16 17:59
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
8	0	174/\$.ccls. and "SiOC-H"	USPĀT;	2004/06/16 18:00
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	, ,
9	3	(semiconductor or die or chip or IC) and	USPAT;	2004/06/16 18:00
		"SiOC-H"	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
10	69	(semiconductor or die or chip or IC) and	USPAT;	2004/06/16 18:00
10		"SiOCH"	US-PGPUB;	2001, 00, 10 10.00
		0100	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
11	6	257/758 and "SiOCH"	USPĀT;	2004/06/16 18:01
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		057/0	IBM_TDB	0004/06/16 10 0:
12	43	257/\$.ccls. and "SiOCH"	USPAT;	2004/06/16 18:04
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
13	48	438/\$.ccls. and "SiOCH"	USPAT;	2004/06/16 18:04
		, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	877	wafer and 257/48	USPAT	2004/06/14 01:20
-	1554	257/48	USPAT	2004/06/14 00:38
-	1	"4968931".PN.	USPAT	2004/06/14 01:01
-	1	"5504369".PN.	USPAT	2004/06/14 01:02
-	1	"5898186". PN.	USPAT	2004/06/14 01:02
_	1	"5962868".PN.	USPAT	2004/06/14 01:05

-	1	"6057171".PN.	USPAT	2004/06/14 01:05
-	1	"6175125".PN.	USPAT	2004/06/14 01:05
_	1	"6218848".PN.	USPAT	2004/06/14 01:05
l _	1	"6281696".PN.	USPAT	2004/06/14 01:06
_	1	"6362638".PN.	USPAT	2004/06/14 01:06
-	1	"5292343". PN.	USPAT	2004/06/14 01:08
-	1	"5389556".PN.	USPAT	2004/06/14 01:09
-	1	"5391188".PN.	USPAT	2004/06/14 01:10
-	1	"5489538".PN.	USPAT	2004/06/14 01:10
_	1	"5532174".PN.	USPAT	2004/06/14 01:10
l _	1	"5600257".PN.	USPAT	2004/06/14 01:11
_	1	"5532174".PN.	USPAT	2004/06/14 01:11
				1
-	1	"5241266".PN.	USPAT	2004/06/14 01:17
_	1	"5254942".PN.	USPAT	2004/06/14 01:17
-	1	"5329471".PN.	USPAT	2004/06/14 01:18
-	1	"5396170".PN.	USPAT	2004/06/14 01:18
_	1	"5396170".PN.	USPAT	2004/06/14 01:18
_	1	"5408129".PN.	USPAT	2004/06/14 01:18
_	1	"5898186".PN.	USPAT	2004/06/14 01:18
4	1			
-	1	"6233184".PN.	USPAT	2004/06/14 01:18
-	1	"6404660".PN.	USPAT	2004/06/14 01:19
-	1	"6411116".PN.	USPAT	2004/06/14 01:19
_	1	"6504359".PN.	USPAT	2004/06/14 01:20
_	47	"5389556"	USPAT	2004/06/14 01:24
_	33	"5532174"	USPAT	2004/06/14 01:24
	i .	***==		
-	9	"5327074"	USPAT	2004/06/14 02:56
-	613440	switch	USPAT	2004/06/14 02:56
-	40223	switch\$3 near transistor	USPAT	2004/06/14 02:56
_	28311	switch\$3 adj transistor	USPAT	2004/06/14 02:57
_	21862	switching adj transistor	USPAT	2004/06/14 03:13
_	25	(switching adj transistor) and 257/48	USPAT	2004/06/14 02:57
_	6	switching adj transistor with pad with		2004/06/14 02:37
-	ا ا		USPAT	2004/00/14 03:14
		(chip or dice or die)		0004/05/5: 55 55
-	1383	257/734	USPAT	2004/06/14 05:20
-	591	257/620	USPAT	2004/06/14 05:20
l _	798	257/620	USPAT;	2004/06/14 05:22
1		·	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1917	257/691	USPAT;	2004/06/14 05:24
1			US-PGPUB;	
			EPO; JPO;	
1	1		DERWENT;	
1			IBM TDB	
	E 40	257/665		2004/06/14 05:26
-	540	257/665	USPAT;	2004/06/14 05:26
			US-PGPUB;	
1	1		EPO; JPO;	<u> </u>
1			DERWENT;	
			IBM TDB	
l _	2317	257/698	USPAT;	2004/06/14 05:36
1	1 2311		US-PGPUB;	= 001, 00, 11 00.00
1			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	405	257/698	US-PGPUB;	2004/06/14 05:30
1	1		EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
1	_	257/600 not 257/600	US-PGPUB;	2004/06/14 05:30
-	0	257/698 not 257/698		2004/06/14 05:30
			EPO; JPO;	
1		· ·	DERWENT;	
			IBM TDB	
_	1912	257/698 not 257/698	USPAT;	2004/06/14 05:34
	1,12	20,,050 1100 25,,050	US-PGPUB;	=====================================
I			1	
			EPO; JPO;	
	;		DERWENT;	
	:		1	

-	4	5494859.pn. or 6037664.pn.	USPAT;	2004/06/14 05:35
ļ			US-PGPUB;	
i			EPO; JPO;	
			DERWENT;	
_	3299	257/773	IBM_TDB USPAT;	2004/06/14 05:45
	3299	237,773	US-PGPUB;	2004/06/14 05:45
			EPO; JPO;	
			DERWENT;	·
			IBM TDB	
_	2690	257/773	USPAT	2004/06/14 05:37
_	609	257/773 not 257/773	USPAT;	2004/06/14 05:39
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	849	257/735	USPĀT;	2004/06/14 05:49
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	678	257/741	USPĀT;	2004/06/14 05:51
			US-PGPUB;	
			EPO; JPO;	
[DERWENT;	
	_		IBM_TDB	
l –	2	5913147.pn.	USPAT;	2004/06/14 05:50
			US-PGPUB;	
į			EPO; JPO;	
			DERWENT;	
	07.64	400/14	IBM_TDB	0004/06/14 06 00
_	2761	438/14	USPAT;	2004/06/14 06:03
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	396	438/14	US-PGPUB;	2004/06/14 06:01
_	390	430/14	EPO; JPO;	2004/00/14 00.01
			DERWENT;	
			IBM TDB	
_	2365	438/14 not 438/14	USPAT;	2004/06/14 06:03
	2303	1507 11 1100 1507 11	US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
	-		IBM TDB	
-	863	438/462	USPAT;	2004/06/14 06:13
			US-PGPUB;	
			EPO; JPO;	
	j		DERWENT;	
			IBM_TDB	
-	221	·	USPAT;	2004/06/14 07:28
		near "N") same (silicon near dioxide or	US-PGPUB;	
		"Si" near "O.sub.2") same ("Cu" or copper)	EPO; JPO;	
			DERWENT;	
			IBM TDB	0004/06/14 07 44
_	157		USPAT;	2004/06/14 07:44
		near "N") same barrier with (silicon	US-PGPUB;	
		near dioxide or "Si" near "O.sub.2") same	EPO; JPO; DERWENT;	
		("Cu" or copper)	IBM TDB	
l _	5610	324/765	USPAT;	2004/06/14 06:31
_	3010	343/103	US-PGPUB;	2004/00/14 00.31
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1805	324/765	US-PGPUB;	2004/06/14 06:14
		· ·	EPO; JPO;	
			DERWENT;	
			IBM TDB	
		I		·

-	3805	324/765 not 324/765 ·	USPAT;	2004/06/14 06:21
			US-PGPUB;	
			EPO; JPO;	
	!		DERWENT;	
			IBM_TDB	
-	1753	324/765 not 324/765 and wafer	USPAT;	2004/06/14 06:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
-	1004	224/762	IBM_TDB	2004/06/14 06:41
-	1264	324/763	USPAT;	2004/06/14 06:41
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
l <u>-</u>	1290	324/760	USPAT;	2004/06/14 06:46
	1230	321/100	US-PGPUB;	2004/00/14 00:40
			EPO; JPO;	
	ļ		DERWENT;	
			IBM TDB	1
l <u> </u>	2	325/201	USPAT;	2004/06/14 06:50
			US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
-	7	barrier near multi\$4 near (film or layer)	USPAT;	2004/06/14 07:27
		same ("Cu" or copper)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	Ø30
-	10397	barrier near (films or layers) same ("Cu"	USPAT;	2004/06/14 07:27
		or copper)	US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	64	1 '	USPAT;	2004/06/14 07:28
		"Si" near "N") same (silicon near dioxide	US-PGPUB;	
		or "Si" near "O.sub.2") same ("Cu" or	EPO; JPO;	
		copper)) not (barrier with (silicon near	DERWENT;	
		nitride or "Si" near "N") same barrier	IBM_TDB	
		with (silicon near dioxide or "Si" near "O.sub.2") same ("Cu" or copper))		
l _	78		USPAT;	2004/06/14 08:00
_	, ,	near "N") near (film or layer) same	US-PGPUB;	2001,00,11 00.00
		(silicon near dioxide or "Si" near	EPO; JPO;	1 .
		"O.sub.2") near (layer or film) and ("Cu"	DERWENT;	
	1	or copper)	IBM TDB	
-	1	"5162258". PN.	USPĀT	2004/06/14 07:58
-	1	"5812364".PN.	USPAT	2004/06/14 07:59
-	1	"5913126".PN.	USPAT	2004/06/14 07:59
-	1	"5918135".PN.	USPAT	2004/06/14 07:59
-	1	"5920775".PN.	USPAT	2004/06/14 07:59
-	78	barrier with (silicon near nitride or	USPAT;	2004/06/14 08:00
	["Si.sub.3" near "N.sub.4") near (film or	US-PGPUB;	
	1	layer) same (silicon near dioxide or	EPO; JPO;	
		"Si" near "O.sub.2") near (layer or film)	DERWENT;	
		and ("Cu" or copper)	IBM_TDB	2004/06/24 20:03
-	78		USPAT;	2004/06/14 08:01
	1	"Si.sub.3N.sub.4") near (film or layer)	US-PGPUB;	
	1	same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) and ("Cu"	EPO; JPO; DERWENT;	
		or copper)	IBM TDB	
I _	113		USPAT;	2004/06/14 08:16
	113	"Si.sub.3" near "N.sub.4") near (film or	US-PGPUB;	=====================================
	1	layer) same (silicon near dioxide or	EPO; JPO;	
		"Si" near "O.sub.2") near (layer or film)	DERWENT;	
	1	and ("Cu" or copper)	IBM TDB	
-	446		USPAT;	2004/06/14 08:16
	1	"Si.sub.3" near "N.sub.4") near (film or	US-PGPUB;	
	1	layer) same (silicon near dioxide or	EPO; JPO;	
	i	"Si" near "O.sub.2") near (layer or film)	DERWENT;	
		and ("Cu" or copper)	IBM TDB	

-	59		USPAT;	2004/06/14 08:25
		"Si.sub.3" near "N.sub.4") near (film or	US-PGPUB;	
1		layer) same (silicon near dioxide or	EPO; JPO;	
		"Si" near "O.sub.2") near (layer or film)	DERWENT;	
		same (passivation or protective or cover)	IBM TDB	
		near (layer or film) and ("Cu" or copper)	100-100	
	ر م		HODAM.	0004/06/16 11-17
-	93	(silicon near nitride or "Si.sub.3" near	USPAT;	2004/06/16 11:17
		"N.sub.4") near (film or layer) same	US-PGPUB;	
		(silicon near dioxide or "Si" near	EPO; JPO;	
		"O.sub.2") near (layer or film) same	DERWENT;	
		(passivation or protective or cover) near	IBM TDB	
		(layer or film) and ("Cu" or copper)	15.1_15.5	
	24		HCDMT.	2004/06/14 08:42
-	34		USPAT;	2004/00/14 00:42
		"N.sub.4") near (film or layer) same	US-PGPUB;	
	ļ	(silicon near dioxide or "Si" near	EPO; JPO;	
		"O.sub.2") near (layer or film) same	DERWENT;	
		(passivation or protective or cover) near	IBM TDB	
		(layer or film) and ("Cu" or copper)) not	-	
		(barrier and (silicon near nitride or		
		"Si.sub.3" near "N.sub.4") near (film or		
1		l · · · · · · · · · · · · · · · · · · ·		İ
1		layer) same (silicon near dioxide or		
1		"Si" near "O.sub.2") near (layer or film)		
1		same (passivation or protective or cover)		
1		near (layer or film) and ("Cu" or copper))		
_	3066	silicon near nitride with dielectric near	USPAT;	2004/06/14 09:29
1		constant	US-PGPUB;	
1			EPO; JPO;	
1			· ·	
			DERWENT;	
			IBM_TDB	, ,
-	1831	silicon near nitride with dielectric near	USPAT	2004/06/14 09:38
	•	constant		
-	1	("FSO") with dielectric near constant	USPAT	2004/06/14 09:39
_	lī	("FSO" or "fluonated silicon oxide") with	USPAT	2004/06/14 09:39
		dielectric near constant		=====================================
	4		USPAT	2004/06/14 09:45
-	1	("FSO" or fluonat\$3 near silicon near	OSPAI	2004/00/14 09:45
		oxide) with dielectric near constant		0004/06/53 55 55
-	1	(siliconoxynitride) with dielectric near	USPAT	2004/06/14 09:40
	ļ	constant		
-	183	(bpsg) with dielectric near constant	USPAT	2004/06/14 10:07
-	1605		USPAT	2004/06/14 10:12
_	2141		USPAT	2004/06/14 10:21
1_	987		USPAT	2004/06/14 10:22
1 -			USPAT	2004/06/14 10:22
-	3439	257/758		
-] 3	257/758 and (silicon near nitride or	USPAT;	2004/06/16 11:18
		"Si.sub.3" near "N.sub.4") near (film or	US-PGPUB;	
		layer) same (silicon near dioxide or	EPO; JPO;	
	1	"Si" near "O.sub.2") near (layer or film)	DERWENT;	
	1	same (passivation or protective or cover)	IBM TDB	
	1	near (layer or film) and ("Cu" or copper)	<u>-</u>	
1_	41	I	USPAT;	2004/06/16 11:24
-	1 41			2004/00/10 11.24
	["Si.sub.3" near "N.sub.4") same	US-PGPUB;	
	İ	(silicon near dioxide or "Si" near	EPO; JPO;	
	Ī	"O.sub.2") same (passivation or protective	DERWENT;	
	1	or cover) near (layer or film) and ("Cu"	IBM_TDB	
		or copper)	_	
I _	358	257/758 and (silicon near nitride or	USPAT;	2004/06/16 11:24
		"Si.sub.3" near "N.sub.4") same	US-PGPUB;	=====================================
	Ī	(silicon near dioxide or "Si" near		
			EPO; JPO;	
		"O.sub.2") and ("Cu" or copper)	DERWENT;	
			IBM_TDB	1
-	553	257/758 and (silicon near nitride or	USPAT;	2004/06/16 15:13
		"Si.sub.3" near "N.sub.4") and (silicon	US-PGPUB;	
	1	near dioxide or "Si" near "O.sub.2") and	EPO; JPO;	
		("Cu" or copper)	DERWENT;	
		(ca or cobber)		
	_	""	IBM_TDB	2004/06/16 12 15
-	2	"20030003765"	USPAT;	2004/06/16 12:45
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	l .		IBM TDB	}
			·	<u> </u>

	0050	055 /550		0004/00/00 40 40
-	2253	257/758 and ("Cu" or copper)	USPAT;	2004/06/16 13:16
			US-PGPUB;	
[EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1700	(257/758 and ("Cu" or copper)) not	USPĀT;	2004/06/16 16:16
		(257/758 and (silicon near nitride or	US-PGPUB;	
		"Si.sub.3" near "N.sub.4") and (silicon	EPO; JPO;	
		near dioxide or "Si" near "O.sub.2") and	DERWENT;	
		("Cu" or copper))	IBM TDB	
_	382		USPAT;	2004/06/16 15:56
	302	"Si.sub.3" near "N.sub.4") and (silicon	US-PGPUB;	2004/00/10 15.50
			EPO; JPO;	
		("Cu" or copper)	DERWENT;	
			IBM_TDB	00044054555
-	182		USPAT;	2004/06/16 16:07
		"Si.sub.3" near "N.sub.4") and (silicon	US-PGPUB;	
		near dioxide or "Si" near "O.sub.2") and	EPO; JPO;	
		("Cu" or copper)	DERWENT;	
			IBM_TDB	
_	791	257/758 and (silicon near nitride or	USPAT;	2004/06/16 16:08
		"Si.sub.3" near "N.sub.4") and (silicon	US-PGPUB;	
		near dioxide or "Si" near "O.sub.2")	EPO; JPO;	
		, , , , , , , , , , , , , , , , , , , ,	DERWENT;	
			IBM TDB	
	802	257/758 and (silicon near nitride or	USPĀT;	2004/06/16 16:08
_	802	"Si.sub.3" near "N.sub.4" or "SiN") and	US-PGPUB;	2004/00/10 10:00
		(silicon near dioxide or "Si" near	EPO; JPO;	
1			DERWENT;	
		"O.sub.2")		
	500	057 (750) 1 (11)	IBM_TDB	2004/06/16 16 22
-	590		USPAT;	2004/06/16 16:09
		"Si.sub.3" near "N.sub.4" or "SiN") and	US-PGPUB;	
		(silicon near dioxide or "Si" near	EPO; JPO;	
		"O.sub.2" or "SiO") and ("Cu" or copper)	DERWENT;	
	1		IBM_TDB	
-	37		USPAT;	2004/06/16 16:09
		"Si.sub.3" near "N.sub.4" or "SiN") and	US-PGPUB;	
		(silicon near dioxide or "Si" near	EPO; JPO;	
		"O.sub.2" or "SiO") and ("Cu" or copper)	DERWENT;	
1) not (257/758 and (silicon near nitride	IBM TDB	
		or "Si.sub.3" near "N.sub.4") and	_	
		(Silicon near dioxide or "Si" near	1	
		"O.sub.2") and ("Cu" or copper))		
l _	1612		USPAT;	2004/06/16 17:47
-	1012	copper))	US-PGPUB;	2001,00,10 17.14,
		Copper))	EPO; JPO;	
1				
			DERWENT;	
L	l		IBM_TDB	I